BORN SEMICONDUCTOR

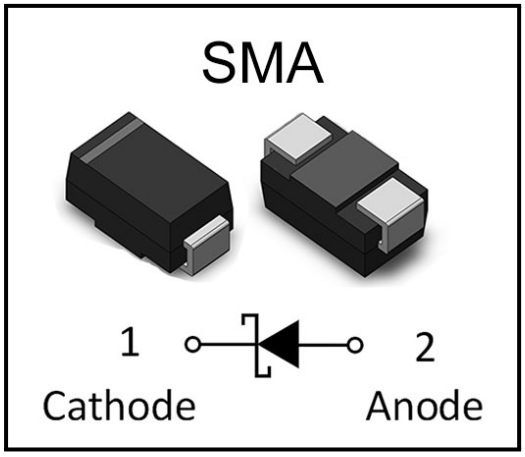
SS22-SS220

Schottky Barrier Diode

Features

- For surface mounted applications
- Matal silicon junction,majority carrier conduction
- Low power loss,high efficiency
- Buit-in strain relief,ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed: 250°C/10 seconds at terminals

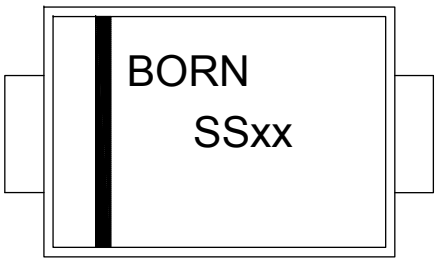
Package



Description

- Case: JEDEC DO-214AC molded plastic
- Terminals:Axial leads.Solderable per MIL-STD-750 Method 2026
- Polarity: Color band denotes cathode
- Mounting Position:Any

Marking



Ordering information

Part Number	SS22	SS23	SS24	SS25	SS26	SS28	SS29	SS210	SS215	SS220
Marking	SS22	SS23	SS24	SS25	SS26	SS28	SS29	SS210	SS215	SS220
Base qty	5K	5K	5K	5K	5K	5K	5K	5K	5K	5K

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Maximum Ratings and Electrical Characteristics@T_A=25°C unless otherwise noted

Symbol	Parameters	SS 22	SS 23	SS 24	SS 25	SS 26	SS 28	SS 29	SS 210	SS 215	SS 220	Units
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	60	80	90	100	150	200	V
V_{RMS}	Maximum RMS Voltage	14	21	28	35	42	56	63	70	105	140	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	60	80	90	100	150	200	V
$I_{F(AV)}$	Maximum average forward Rectified Current	2.0										A
I_{FSM}	Non-repetitive peak forward surge current 8.3 ms singlehalf sine-wave	50										A
V_F	Forward Voltage@I_F=2.0A	0.55			0.70		0.85			0.95		V
I_R	Peak Reverse current at T_A=25°C	0.50					0.10					mA
	Rated DC Blocking Voltage T_A=100°C	10					5					
T_J	Operating Temperature Range	-55 to +150										°C
T_{STG}	Storage Temperature Range	-55 to +150										°C
$R_{\theta JA}$	Thermal Resistance(1)	75										°C/W
$R_{\theta JL}$		17										

Note:(1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2” x 0.2” (5.0 mm x 5.0 mm) copper pad areas

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Typical Performance Characteristics(T_J=25°C, unless otherwise noted)

Figure 1:I_O-T_L Curve

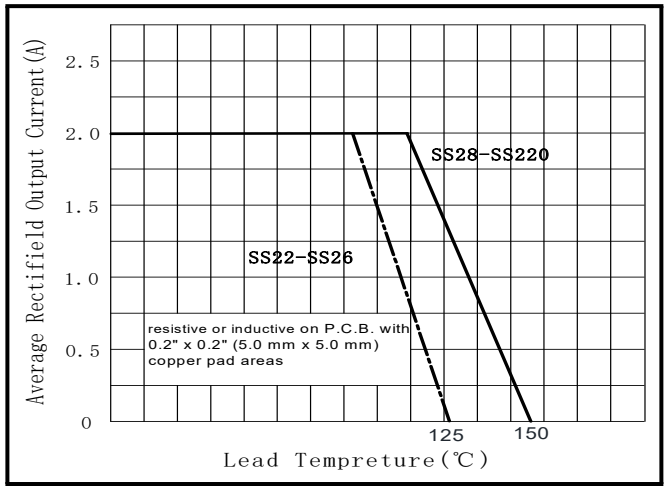


Figure 2:Surge Forward Current Capability

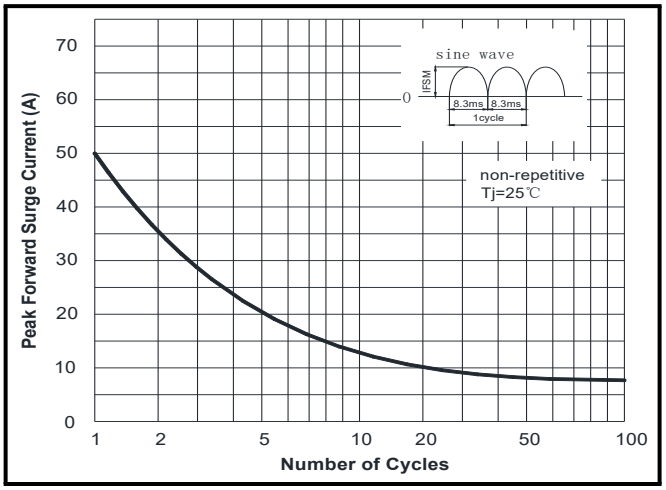


Figure 3:Forward Voltage

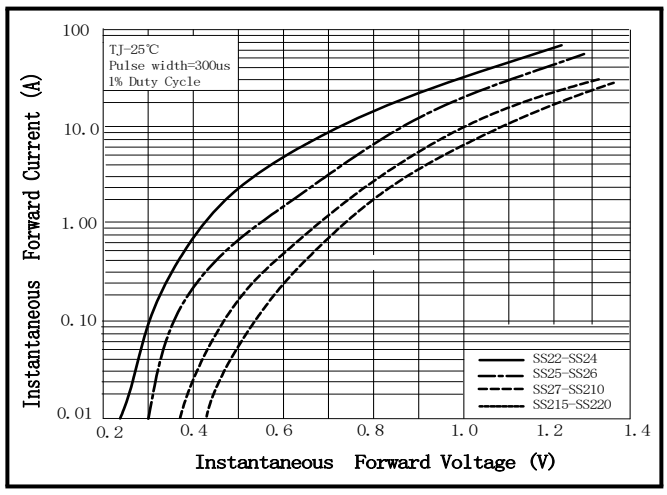
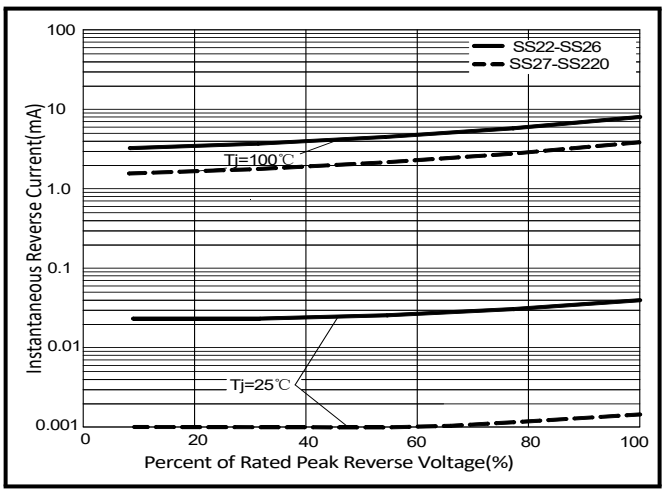


Figure 4:Typical Reverse Characteristics



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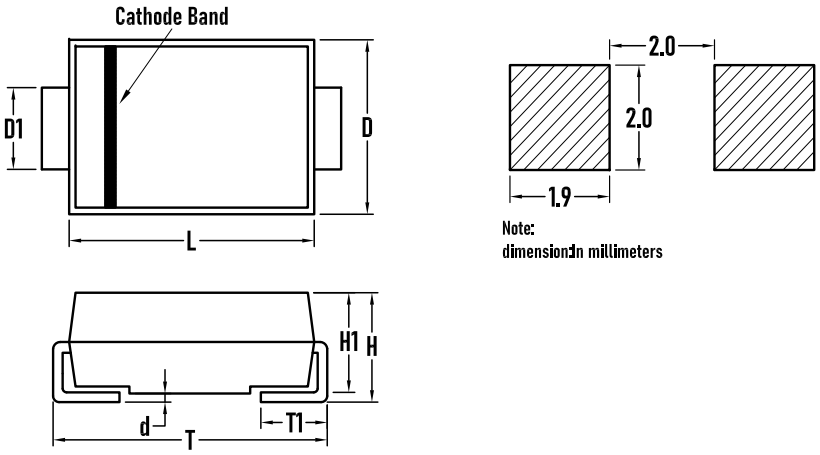
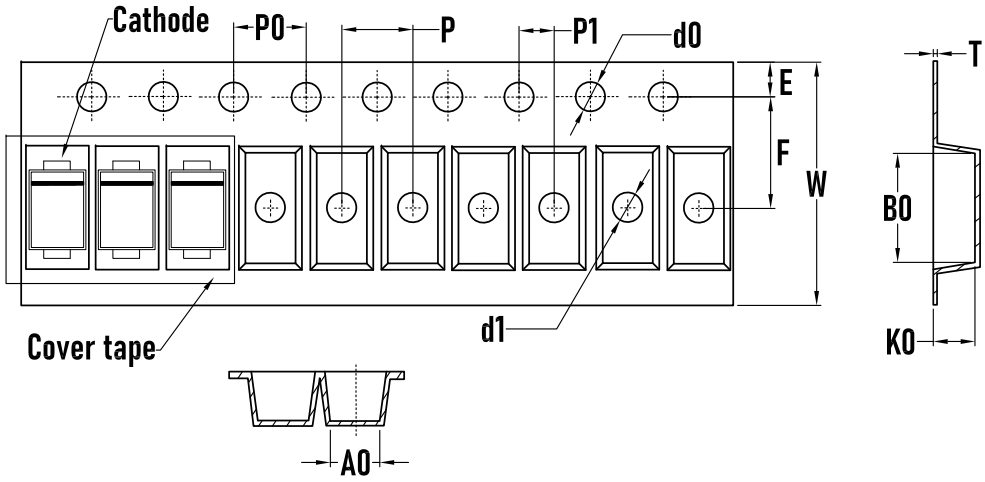
Outline Drawing - SMA



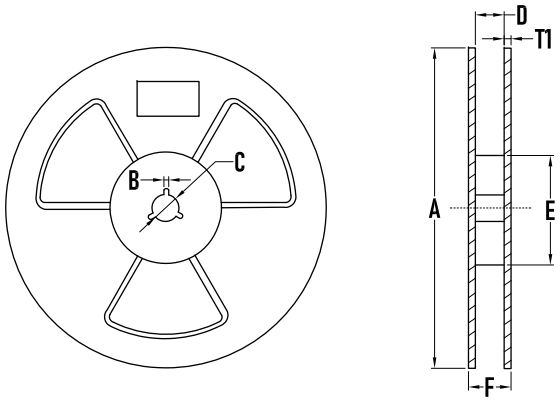
SYMBOL	MILLIMETER		Inches	
	MIN.	MAX.	MIN.	MAX.
D	2.5	2.9	0.098	0.114
D1	1.2	1.8	0.047	0.071
T	4.8	5.3	0.189	0.209
T1	0.8	1.5	0.031	0.059
d	–	0.2	–	0.008
H1	1.8	2.2	0.071	0.087
H	1.9	2.5	0.075	0.098
L	3.9	4.6	0.154	0.181

Packaging Tape - SMA



SYMBOL	MILLIMETER
A0	2.70
B0	5.10±0.1
d0	1.50±0.1
d1	1.50±0.1
E	1.75±0.1
F	5.50±0.1
K0	2.40±0.1
P	4.00±0.1
P0	4.00±0.1
P1	2.00±0.1
W	12.00±0.1
T	0.2±0.02

Packaging Reel



SYMBOL	MILLIMETER
A	323±2
B	3.0±0.2
C	15.0±0.5
D	13±2
E	73±2
T1	2.2±0.2
Quantity	5000PCS

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